

## MOSFET chip DMOST165-01

### Description

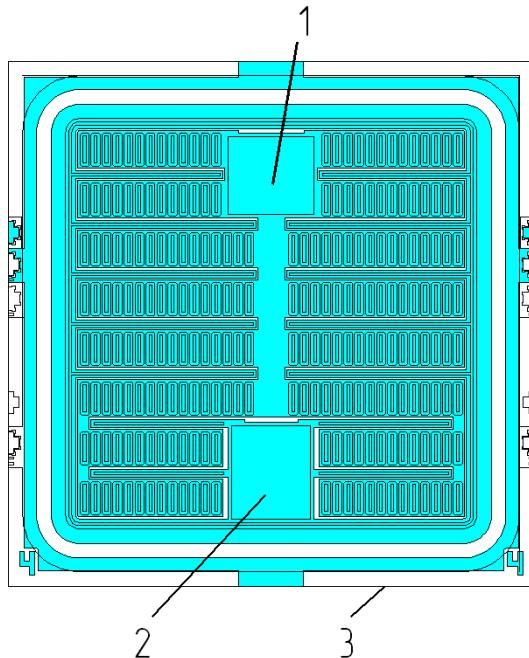
MOSFET chip with internal channel (normally-on) DMOST165-01 is designed to be used in hybrid microchips and packaged field-effect transistors.

### Features

- Chip size – 1.44 x 1.44 mm
- Chip thickness – 0.42±0.02 mm
- Contact pads size:  
Gate – 0.23 x 0.21 mm  
Source – 0.22 x 0.25 mm
- Metallization: top – AlSi,  
bottom – CrAu for bonding on  
conductive adhesive

### Absolute maximum rating

Maximum Temperature	
Storage Temperature	- 55 °C to 150 °C
Operating Junction Temperature	- 40 °C to 100 °C
Maximum Voltage	
Drain-to-Source Voltage	370 V
Gate-to-Source Voltage	20 V



1 - Gate

2 - Source

3 - Drain

### Electrical Characteristics ( $T_A = 25^\circ\text{C}$ )

Parameter	Symbol	Unit	Min.	Typ.	Max.	Conditions
Drain-to-Source ON-State Resistance	$R_{DS}$	Ohm			25	$V_{GS} = 0 \text{ V}, I_D = 100 \text{ mA}$
Drain Leakage Current	$I_{LEAK.D}$	$\mu\text{A}$			0.1	$V_{GS} = - 4 \text{ V}, V_{DS} = 350 \text{ V}$
Gate Leakage Current	$I_{LEAK.G}$	$\mu\text{A}$			0.1	$V_{GS} = - 20 \text{ V}$
LED Constant Forward Voltage (drain <sup>-</sup> , source <sup>+</sup> )	$V_{SD}$	V			1.0	$V_{GS} = - 4.5 \text{ V}, I_S = 150 \text{ mA}$